Electronic Supplementary Information for

## Topology Design of Digital Metamaterials for Ultra-Compact Integrated Photonic Devices Based on Mode Manipulation

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	Air	Silicon		Air	Silicon
2D designs					
TE0-to-TE1	556	2027	TE0-to-TE2	613	1970
TE0-to-TE3	554	2029	TE1-to-TE2	628	1955
TE1-to-TE3	341	2242	TE2-to-TE3	374	2209
Diode	760	1823	Demultiplexer	1046	2923
Quasi-3D designs					
TE0-to-TE1	803	1780			
Diode	983	1600	Demultiplexer	834	3135

Table S1. Air and silicon pixel amount in the designed digital metamaterials.

**Table S2.** Comparison between Ref. 1 and this work. Footprint and transmission efficiencies at center wavelength obtained from 2D simulations are listed for six mode conversions. It is noted that the distribution of refractive index (RI) in Ref. 1 had continuous regions, while in our design only air and silicon can be found.

	Footprint	TE0-to-	TE0-to-	TE0-to-	TE1-to-	TE1-to-	TE2-to-
		TE1	TE2	TE3	TE2	TE3	TE3
Ref. 1	1.55λ <sup>2</sup>	99.3%	98.3%	90.6%	96.8%	86.3%	80.1%
	Continuous RI						
This	0.645λ <sup>2</sup>	98.4%	96.7%	88.2%	95.3%	88.7%	85.3%
work	Binary RI						

**Table S3.** Comparison between reported TE0-to-TE1 mode converter and this work.Transmission efficiencies at center wavelength obtained from 3D simulations are listed.

	Scheme	Footprint	TE0-to-TE1 (3D)	
Ref. 2	Photonic	~6.3µm×3.2µm	3D Opt: ~80%	
	crystal		Quasi-3D Opt: ~60%	
Ref. 3	Taper	~18.6µm×2.8µm	98.6%	
	waveguide			
Ref. 4	Ge/Si	1.0μm×1.55μm	~91%	
	pattern			
<b>Ref. 5</b> Digital 1.1µm×2.3µm		57%		
	metamaterial	1.0μm×3.1μm	37%	
This	Digital	1.0μm×1.55μm	52.7%	
work	metamaterial			

**Table S4.** Comparison between reported reciprocal optical diodes and this work. Footprint, transmission efficiencies at center wavelength and contrast ratio  $(T_{forw}/T_{back})$  obtained from 3D simulations are listed.

	Scheme	Footprint	Forward (3D)	Backward (3D)	Contrast ratio
Ref. 6	Ag splitter	4.0μm×0.65μm	62%	0.3%	206
Ref. 7	Partially	7.0μm×1.0μm	62%	0.53%	117
	etching				
Ref. 8	Digital	3.0µm×3.0µm	TE: 71.1%	1.8%	40
	metamaterial		TM: 91.1%	3.2%	28.5
Ref. 5	Digital	1.1μm×2.3μm	57%	1.8%	32
	metamaterial	1.0μm×3.1μm	37%	0.9%	41
This	Digital	1.0μm×1.55μm	43.1%	0.47%	91.7
work	metamaterial				

**Table S5.** Comparison between inversely designed mode-order demultiplexers and this work. Channel number, footprint, insertion loss at center wavelength and contrast ratio obtained from 3D simulations are listed.

	Channel number	Footprint	Insertion loss (3D)	Contrast ratio
Ref. 9	2	4.22μm×2.6μm	-0.25dB	~17dB
	3	6.08µm×4.93µm		
<b>Ref. 10</b>	4	5.4µm×6.0µm	< <b>-</b> 1.5dB	18 dB
Ref. 11	3	3.6µm *4.8µm	< <b>-</b> 1.5dB	22dB
This	2	1.55µm×1.55µm	-2.2dB	14.7dB
work				



Figure S1. Designs for mode converters (TE0-to-TE1 and TE0-to-TE2) with 50nm pixels and

corresponding magnetic fields simulated at center wavelength.



**Figure S2.** Contrast ratio of reciprocal optical diode with random errors. (b) Structure and magnetic field of a diode sample with 3% error. This sample is the one with the lowest contrast ratio among 8 samples with 3% error percentage.



**Figure S3.** Contrast ratio and transmission efficiencies of demultiplexer with random errors. (b) Structure and magnetic field of a diode sample with 3% error. This sample is the one with the lowest contrast ratio among 5 samples with 3% error percentage.

## References

- 1. J. Lu, J. Vuckovic, Objective-first design of high-efficiency, small-footprint couplers between arbitrary nanophotonic waveguide modes, Opt. Express 20 (2012) 7221.
- L.H. Frandsen, Y. Elesin, L.F. Frellsen, M. Mitrovic, Y. Ding, O. Sigmund, K. Yvind, Topology optimized mode conversion in a photonic crystal waveguide fabricated in silicon-on insulator material, Opt. Express 22 (2014) 8525.
- D. Chen, X. Xiao, L. Wang, Y. Yu, W. Liu, Q. Yang, Low-loss and fabrication tolerant silicon mode order converters based on novel compact tapers, Opt. Express 23 (2015) 11152.
- H. Ye, F. Yu, Y. Liu, Z. Yu, J. Li, D.F. Zhu, B.D. Su, W.B. Xu, Ultra-Compact Waveguide-Integrated TE-Mode Converters With High Mode Purity by Designing Ge/Si Patterns, IEEE Photon. J. 11 (2019) 6602208
- 5. F. Callewaert, S. Butun, Z. Li, K. Aydin, Inverse design of an ultra-compact broadband optical diode based on asymmetric spatial mode conversion, Sci. Rep. 6 (2016) 32577.
- 6. J. Li, H. Ye, Z. Yu, Y. Liu, Design of a broadband reciprocal optical diode in a silicon waveguide assisted by silver surface plasmonic splitter, Opt. Express 25 (2017) 19129.
- D. Zhu, J. Zhang, H. Ye, Z. Yu, Y. Liu, Design of a broadband reciprocal optical diode in multimode silicon waveguide by partial depth etching, Opt. Commun. 418 (2018) 88.
- B. Shen, R. Polson, R. Menon, Integrated digital metamaterials enables ultra-compact optical diodes, Opt. Express 23 (2015) 10847.
- L.F. Frellsen, Y. Ding, O. Sigmund, L.H. Frandsen, Topology optimized mode multiplexing in silicon-on-insulator photonic wire waveguides, Opt. Express 24 (2016) 16866.
- H. Xie, Y. Liu, S. Wang, Y. Wang, Y. Yao, Q. Song, J. Du, Z. He, K. Xu, Highly Compact and Efficient Four-Mode Multiplexer Based on Pixelated Waveguides, IEEE Photon. Technol. Lett. 32 (2020) 166.
- W. Chang, L. Lu, X. Ren, L. Lu, M. Cheng, D. Liu, .M.M. Zhang, An Ultracompact Multimode Waveguide Crossing Based on Subwavelength Asymmetric Y-Junction, IEEE Photon. J. 10 (2018) 4501008.